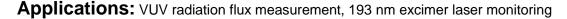


VUV photodiode

General Features:

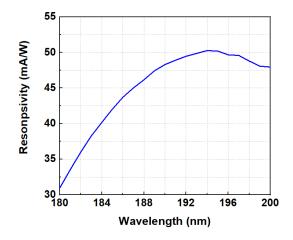
- SiC-based vacuum ultraviolet (VUV) photodiode
- Excellent stability under high fluence VUV exposure
- Photovoltaic mode operation
- Visible blind and low dark current
- High detection efficiency for 193 nm VUV radiation
- Ceramic package



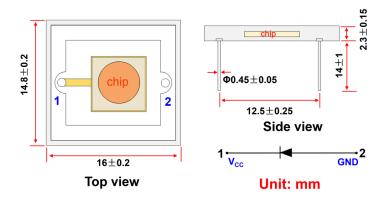
Specifications:

Parameters	Symbol	Value	Unit
Maximum ratings			
Operation temperature range	T_{opt}	-20-80	°C
Storage temperature range	T _{sto}	-55-90	°C
Soldering temperature (3 s)	T _{sol}	260	°C
Maxium reverse voltage	$V_{r\text{-max}}$	-20	V
Electro-Optical characteristics (25 °C)			
Effective photo-sensitive area	А	19.6	mm²
Responsivity (@193 nm)	R	50	mA/W
Dark current (@-1 V)	I _d	< 100	pA
Shunt resistance (@±10 mV)	R _{sh}	> 10	GΩ
Capacitance (@ 0 V and 1 MHz)	C _p	565	pF
Rise time ($V_r=0 \text{ V}, \text{ R}_L=50 \Omega$)	t _r	< 1	μS

Spectral response



Package dimensions



Model: SCT-VUV20